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GUJARAT TECHNOLOGICAL UNIVERSITY BE - SEMESTER-VI (NEW) - EXAMINATION – SUMMER 2016 Subject Code:2160709 Date:17/05/2010 Subject Name: Embedded & VLSI Design Time: 10:30 AM to 01:00 PM Time: 10:30 AM to 01:00 PM Total Marks: 7 Instructions: 1. Attempt all questions.			
	2. 3.	Make suitable assumptions wherever necessary.	
Q.1	(a) (b)	Explain step by step fabrication of n-well CMOS along with necessary figures. Classify Embedded systems along with their applications.	07 07
Q.2	(a) (b)	Derive drain current equation for n-channel MOSFET in linear mode. Explain different types of processors used in Embedded systems. OR	07 07
	(b)	Explain parallel, serial and wireless communication interface using at least one example for each interface.	07
Q.3	(a) (b)	Explain different operation modes of MOS with figures. Explain various types of Embedded system memories. OR	07 07
Q.3	(a)	Explain semi custom Design and Full custom Design along with circuit performance and technology window.	07
Q.4	(b) (a)	Write a short note on built in self test. Derive equation of V_{IL} and V_{IH} for n-type MOSFET inverter with depletion type	07 07
	(b)	load. Write a brief note on Unified Modeling Language (UML). OR	07
Q.4	(a)	Define and discuss Latch-up problem in CMOS inverter. Mention causes for latch-up and guidelines for avoiding latch-up.	07
	(b)	Define controllability and observability. List out electrical and logical faults observed in circuit.	07
Q.5	(a) (b)	Define sequential circuits and implement CMOS clocked JK latch. Give a brief note on different phases of Embedded Development Life Cycle. OR	07 07
Q.5	(a) (b)	Implement the function $F = (A (B+C) + DE)'$ in CMOS. Consider a CMOS inverter circuit with the following parameters: $V_{DD} = 3.3 V$, For NMOS $V_{TO, n} = 0.6 V$, $\mu_n C_{ox} = 60 \mu A/V^2$, $(W/L)_n = 8$ For PMOS $V_{TO, p} = -0.7 V$, $\mu_p C_{ox} = 25 \mu A/V^2$, $(W/L)_p = 12$. Calculate noise margin of the circuit.	07 07
